

Thyristor Module

$$V_{RRM} = 1400 \text{ V}$$

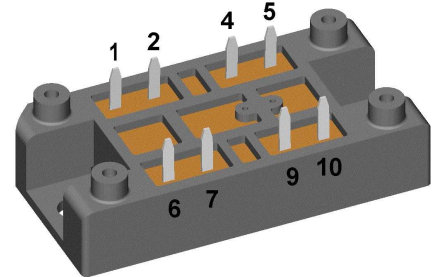
$$I_{TAV} = 27 \text{ A}$$

$$V_T = 1.28 \text{ V}$$


AC Controlling
 2~ full-controlled

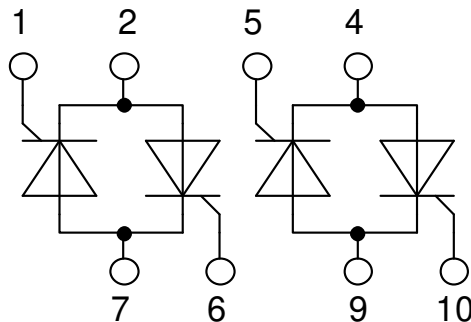
Part number

VW2x60-14io1



Backside: isolated

 E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al₂O₃-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: V1-A-Pack

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Height: 17 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

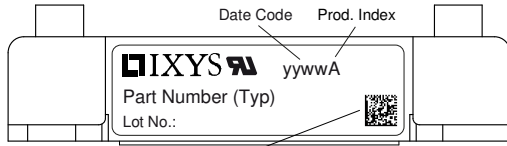
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Rectifier			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1500	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1400	V
I_{RD}	reverse current, drain current	$V_{R/D} = 1400 V$	$T_{VJ} = 25^{\circ}C$		100	μA
		$V_{R/D} = 1400 V$	$T_{VJ} = 125^{\circ}C$		5	mA
V_T	forward voltage drop	$I_T = 40 A$	$T_{VJ} = 25^{\circ}C$		1.25	V
		$I_T = 80 A$			1.65	V
		$I_T = 40 A$	$T_{VJ} = 125^{\circ}C$		1.28	V
		$I_T = 80 A$			1.75	V
I_{TAV}	average forward current	$T_C = 85^{\circ}C$	$T_{VJ} = 125^{\circ}C$		27	A
I_{RMS}	RMS forward current per phase	180° sine			60	A
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 125^{\circ}C$		0.85	V
r_T	slope resistance				11	m Ω
R_{thJC}	thermal resistance junction to case				0.92	K/W
R_{thCH}	thermal resistance case to heatsink			0.3		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		110	W
I_{TSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		520	A
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		560	A
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 125^{\circ}C$		440	A
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		475	A
I^2t	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		1.35	kA ² s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		1.31	kA ² s
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 125^{\circ}C$		970	A ² s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		940	A ² s
C_J	junction capacitance	$V_R = 400 V \quad f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		64	pF
P_{GM}	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 125^{\circ}C$		10	W
		$t_p = 300 \mu s$			5	W
P_{GAV}	average gate power dissipation				0.5	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 125^{\circ}C; f = 50 \text{ Hz}$	repetitive, $I_T = 45 A$		100	A/ μs
		$t_p = 200 \mu s; di_G/dt = 0.45 A/\mu s;$ $I_G = 0.45 A; V = \frac{2}{3} V_{DRM}$	non-repet., $I_T = 27 A$		500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty; \text{ method 1 (linear voltage rise)}$	$T_{VJ} = 125^{\circ}C$		1000	V/ μs
V_{GT}	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		1.5	V
			$T_{VJ} = -40^{\circ}C$		1.6	V
I_{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		100	mA
			$T_{VJ} = -40^{\circ}C$		200	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^{\circ}C$		0.2	V
I_{GD}	gate non-trigger current				5	mA
I_L	latching current	$t_p = 10 \mu s$	$T_{VJ} = 25^{\circ}C$		450	mA
		$I_G = 0.45 A; di_G/dt = 0.45 A/\mu s$				
I_H	holding current	$V_D = 6 V \quad R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		200	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$		2	μs
		$I_G = 0.45 A; di_G/dt = 0.45 A/\mu s$				
t_q	turn-off time	$V_R = 100 V; I_T = 20 A; V = \frac{2}{3} V_{DRM}$ $di/dt = 10 A/\mu s \quad dv/dt = 15 V/\mu s \quad t_p = 200 \mu s$	$T_{VJ} = 100^{\circ}C$		150	μs



Package V1-A-Pack			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			100	A
T_{VJ}	virtual junction temperature		-40		125	°C
T_{op}	operation temperature		-40		100	°C
T_{stg}	storage temperature		-40		125	°C
Weight				37		g
M_D	mounting torque		2		2.5	Nm
$d_{Spp/App}$	creepage distance on surface	terminal to terminal	6.0			mm
$d_{Spb/Apb}$	striking distance through air	terminal to backside	12.0			mm
V_{ISOL}	isolation voltage	t = 1 second 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	3600			V
		t = 1 minute	3000			V



Data Matrix: Typ (1-19), DC+Prod.Index (20-25), FKT# (26-31)
leer (33), lld.# (33-36)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VW2x60-14io1	VW2x60-14io1	Blister	24	519128

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 125^{\circ}C$

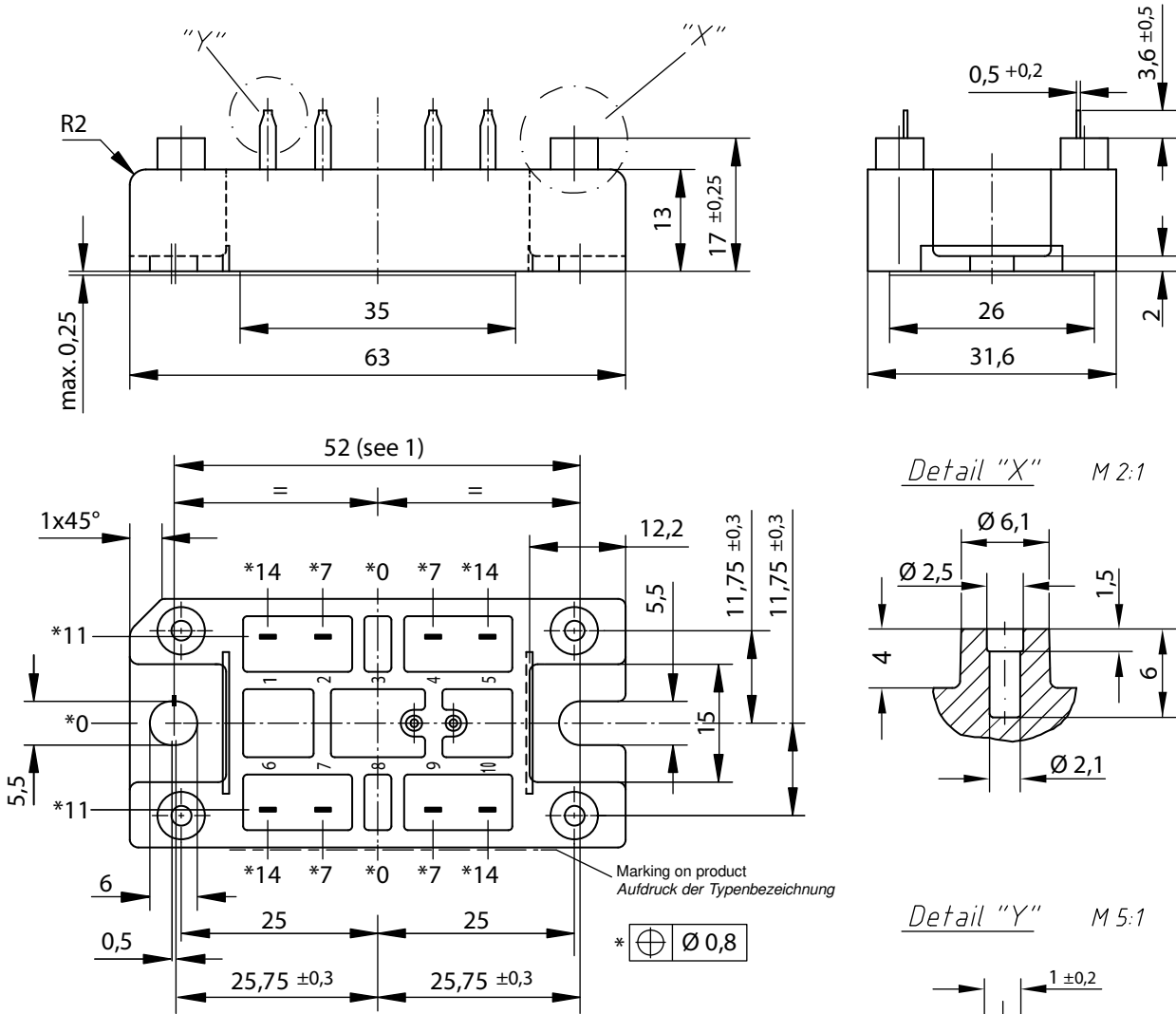


Thyristor

$V_{0\ max}$	threshold voltage	0.85	V
$R_{0\ max}$	slope resistance *	8.5	mΩ

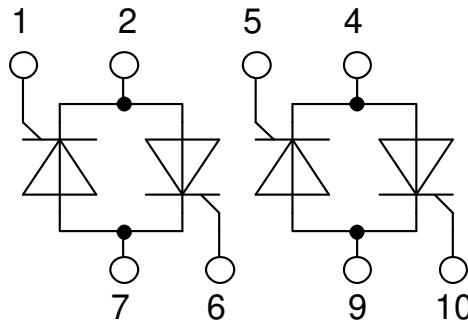


Outlines V1-A-Pack



Remarks / Bemerkungen:

1. Nominal distance mounting screws on heat sink: 52 mm / Nennabstand Befestigungsschrauben auf Kühlkörper: 52 mm
 2. General tolerance / Allgemeintoleranz: DIN ISO 2768 -T1-c
 3. Surface treatment of pins: tin plated (Sn) in hot dip / Oberflächenbehandlung der Pins: verzinkt (Sn) im Tauchbad
 4. Detail X:^L
EJOT PT® self-tapping screws (dimension K25) to be recommended for mounting on PCB^L
selbstschneidende Schraube (Größe K25) empfohlen für die PCB-Montage
- Take care on the maximum screw length according to board thickness and the maximum hole depth of 6 mm^L
Bei der Wahl der Schraubenlänge die PCB-Dicke und die maximale Lochtiefe von 6mm beachten
- Recommended mounting torque: 1.5 Nm / Empfohlenes Drehmoment: 1.5 Nm



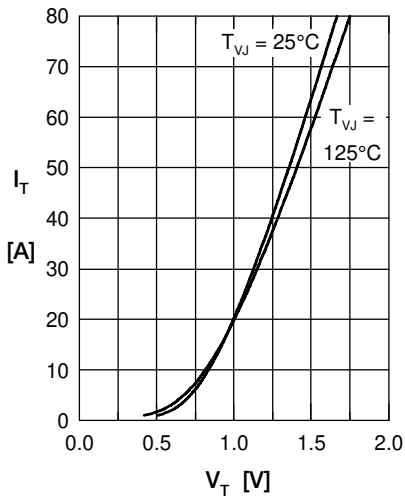
Thyristor


Fig. 1 Forward characteristics

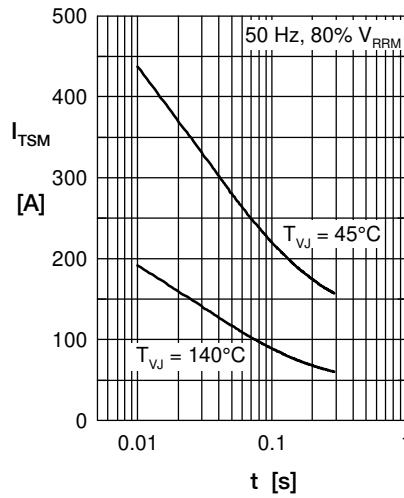
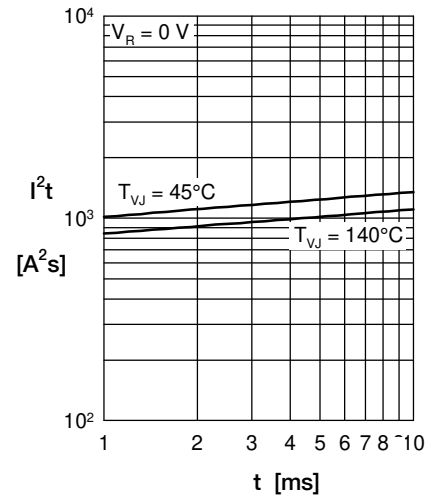
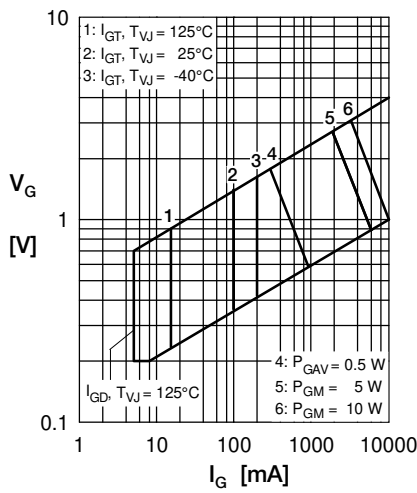

 Fig. 2 Surge overload current I_{TSM} ; crest value, t: duration

 Fig. 3 I^2t versus time (1-10 s)


Fig. 4 Gate voltage & gate current

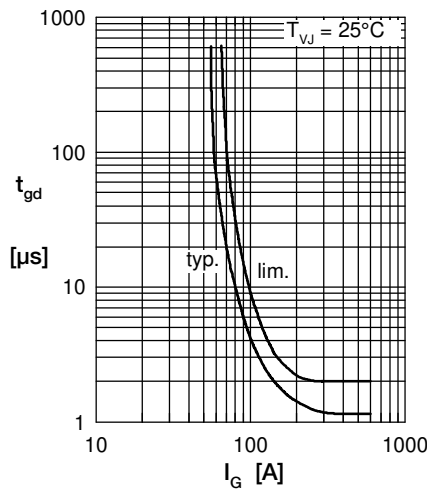
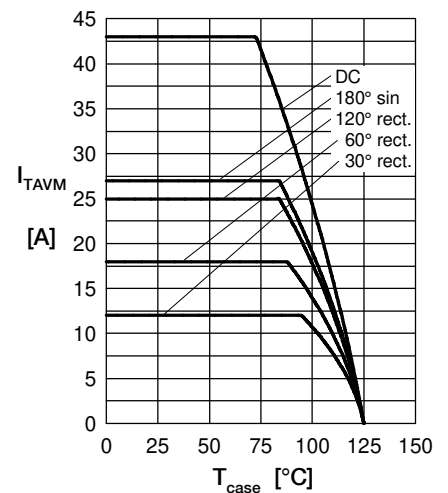

 Fig. 5 Gate controlled delay time t_{gd}


Fig. 6 Max. forward current at case temperature

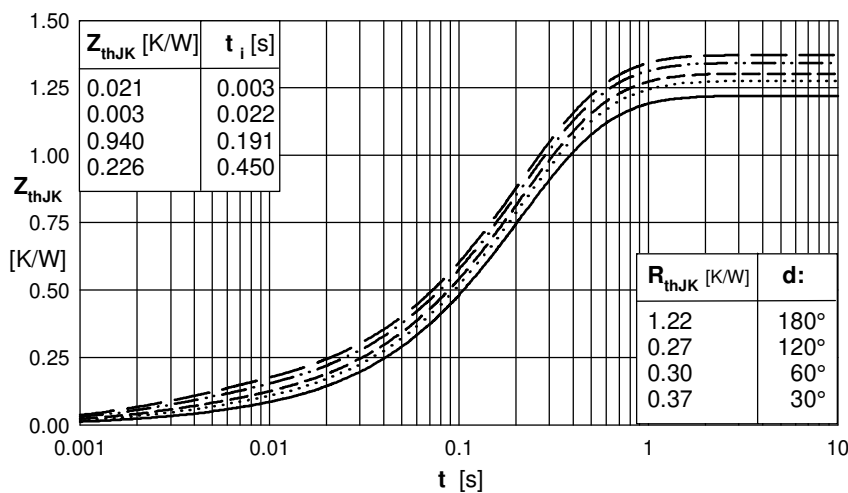


Fig. 7 Transient thermal impedance junction to heatsink (per thyristor)

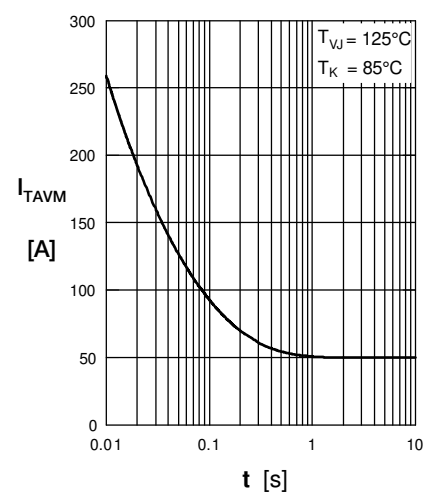


Fig. 8 Rated RMS current vs. time (360° conduction)